



P-Channel 60-V (D-S) MOSFET

Pb-free

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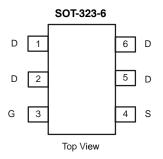
PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^a	Q _g (Typ.)			
-60	0.258 at V _{GS} = 10 V	1.8 ^a	3.5 nC			
	0.390 at V _{GS} = 4.5 V	1.5 ^a	3.3110			

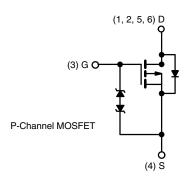
FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS tested
- ESD protection

APPLICATIONS

- Load Switch
- DC/DC converter





PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	-60		
Gate-source voltage	V _{GS} ± 20	± 20	_ v		
Continuous drain current	T _C = 25 °C a	1	-1.8	A	
	T _C = 125 °C	I _D	-1.2		
Continuous source current (diode conducti	on) ^a	I _S	-1.8		
Pulsed drain current ^b		I _{DM}	-6.9		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-8		
Single pulse avalanche energy	L = U. I IIII	E _{AS}	3.3	mJ	
Martin and a distribution b	T _C = 25 °C	Б	3.5	w	
Maximum power dissipation ^b	T _C = 125 °C	P_{D}	0.7		
Operating junction and storage temperature	e range	T _J , T _{sta}	-55 to +150	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount c	R_{thJA}	120	°C/W
Junction-to-foot (drain)		R_{thJF}	42	C/VV

Notes

- a. Package limited
- b. Pulse test; pulse width $\leq 300~\mu\text{s},$ duty cycle $\leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)





SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)								
PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static								
Drain-source breakdown voltage	V_{DS}	V _{GS} = 0 V, I _D = -250 μA		-60	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = -250 μA	-1.5		-3.5	V	
Cata agurag lagkaga		V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$		-	± 5	μΑ	
Gate-source leakage	I _{GSS}	$V_{DS} =$	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 5	mA	
		$V_{GS} = 0 V$	$V_{DS} = -48 \text{ V}$	-	-	-1		
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -48 V, T _J = 125 °C	-	-	-50	μΑ	
		$V_{GS} = 0 V$	$V_{DS} = -48 \text{ V}, T_{J} = 150 ^{\circ}\text{C}$	-	-	-150		
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \le -5 V$	-5	-	-	Α	
		V _{GS} = -10 V	I _D = -2 A	-	0.258	0.289		
Drain-source on-state resistance a	В	V _{GS} = -10 V	$I_D = -2 \text{ A}, T_J = 125 ^{\circ}\text{C}$	-	-	0.355	Ω	
Diain-source on-state resistance ~	R _{DS(on)}	V _{GS} = -10 V	$I_D = -2 \text{ A}, T_J = 150 ^{\circ}\text{C}$	-	-	0.438		
		V _{GS} = -4.5 V	I _D = -1 A	-	0.390	0.450		
Forward transconductance b	g _{fs}	V _{DS} =	-10 V, I _D = -1.5 A	-	3		S	
Dynamic ^b								
Input capacitance	C _{iss}			-	850	-		
Output capacitance	Coss	$V_{GS} = 0 V$	V _{GS} = 0 V V _{DS} = -25 V, f = 1 MHz		76	-	pF	
Reverse transfer capacitance	C _{rss}				38	-		
Total gate charge ^c	Qg			-	3.5	-		
Gate-source charge ^c	Q_{gs}	$V_{GS} = -4.5 \text{ V}$	$V_{DS} = -30 \text{ V}, I_{D} = -1 \text{ A}$	-	1.2	-	nC	
Gate-drain charge ^c	Q_{gd}			-	1.9	=.]	
Gate resistance	R_g	f = 1 MHz		-	5.2	-	Ω	
Turn-on delay time ^c	t _{d(on)}			-	43	68		
Rise time ^c	t _r	$V_{DD} = -30 \text{ V}, \text{ R}_L = 30 \Omega$ $I_D \cong -1 \text{ A}, \text{ V}_{GEN} = -4.5 \text{ V}, \text{ R}_g = 1 \Omega$		-	27	35	ns	
Turn-off delay time ^c	t _{d(off)}			-	12	20		
Fall time ^c	t _f		-	9	15			
Source-Drain Diode Ratings and Characteristics ^b								
Pulsed current a	I _{SM}			-	-	-6.9	Α	
Forward voltage	V_{SD}	I _F = ·	-	-0.8	-1.2	V		

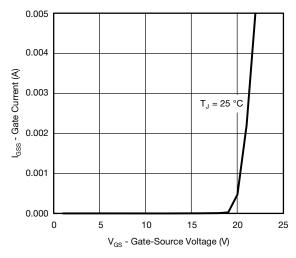
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

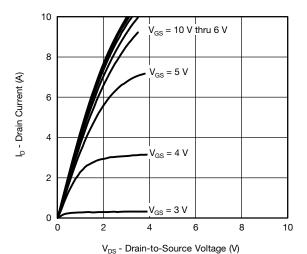
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



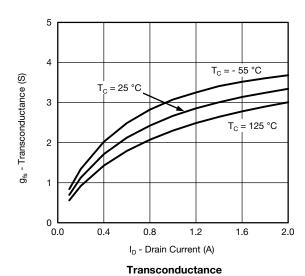
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

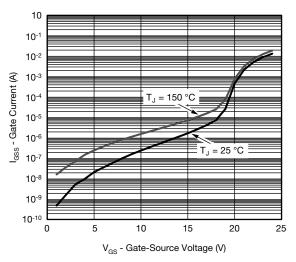


Gate Current vs. Gate-Source Voltage

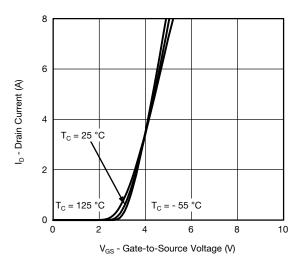


Output Characteristics

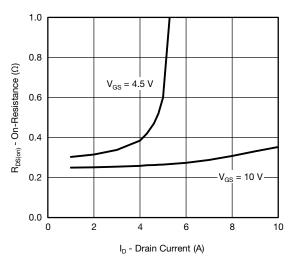




Gate Current vs. Gate-Source Voltage



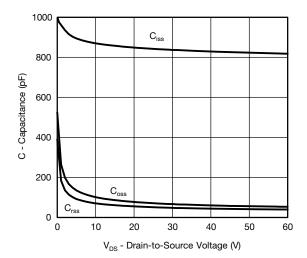
Transfer Characteristics



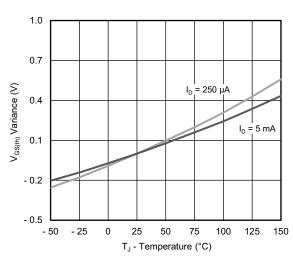
On-Resistance vs. Drain Current



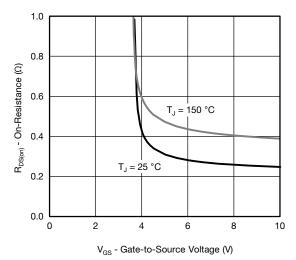
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



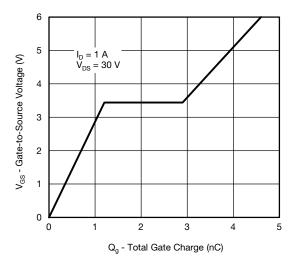
Capacitance



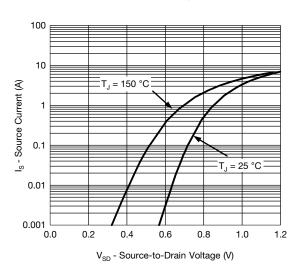
Threshold Voltage



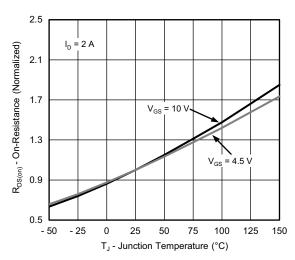
On-Resistance vs. Gate-to-Source Voltage



Gate Charge



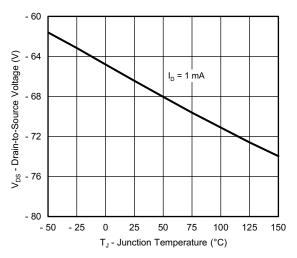
Source Drain Diode Forward Voltage



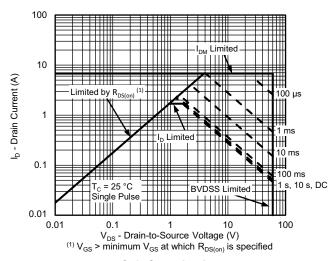
On-Resistance vs. Junction Temperature



TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



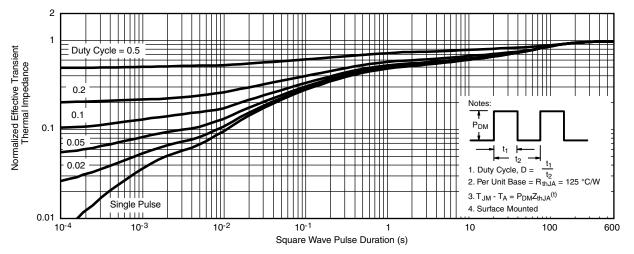
Drain Source Breakdown vs. Junction Temperature



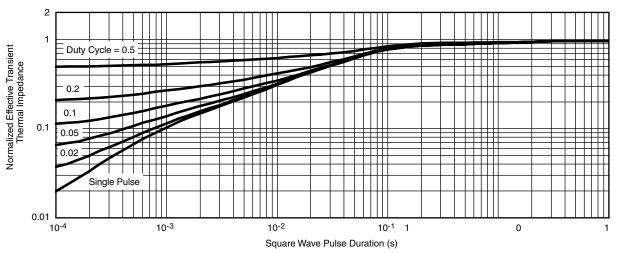
Safe Operating Area



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

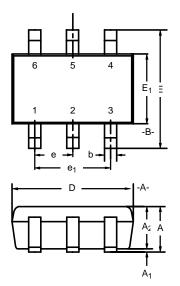
Note

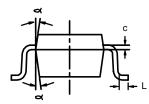
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions





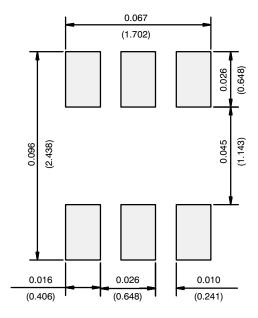




	MILLIMETERS			I	S	
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.90	-	1.10	0.035	-	0.043
A ₁	_	-	0.10	_	_	0.004
A ₂	0.80	-	1.00	0.031	_	0.039
b	0.15	-	0.30	0.006	_	0.012
С	0.10	-	0.25	0.004	-	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
Е	1.80	2.10	2.40	0.071	0.083	0.094
E ₁	1.15	1.25	1.35	0.045	0.049	0.053
е	0.65BSC			0.026BSC		
e ₁	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
8	7°Nom			7°Nom		
	•					



RECOMMENDED MINIMUM PADS FOR SOT323: 6-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)





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